



STB21N65M5, STF21N65M5 STI21N65M5, STP21N65M5, STW21N65M5

N-channel 650 V, 0.175 Ω , 17 A MDmesh™ V Power MOSFET
D²PAK, TO-220FP, TO-220, I²PAK, TO-247

Features

Type	V _{DSS} @ T _{Jmax}	R _{DS(on)} max	I _D	P _W
STB21N65M5	710 V	< 0.190 Ω	17 A	125 W
STF21N65M5			17 A ⁽¹⁾	30 W
STI21N65M5			17 A	125 W
STP21N65M5			17 A	125 W
STW21N65M5			17 A	125 W

1. Limited only by maximum temperature allowed

- Worldwide best R_{DS(on)} * area
- Higher V_{DSS} rating
- High dv/dt capability
- Excellent switching performance
- 100% avalanche tested

Application

- Switching applications

Description

MDmesh V is a revolutionary Power MOSFET technology, which combines an innovative proprietary vertical process with the well known company's PowerMESH™ horizontal layout. The resulting product has an extremely low on-resistance, unmatched among silicon-based Power MOSFETs, making it especially suited for applications which require superior power density and outstanding efficiencies.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB21N65M5	21N65M5	D ² PAK	Tape and reel
STF21N65M5		TO-220FP	Tube
STI21N65M5		I ² PAK	Tube
STP21N65M5		TO-220	Tube
STW21N65M5		TO-247	Tube

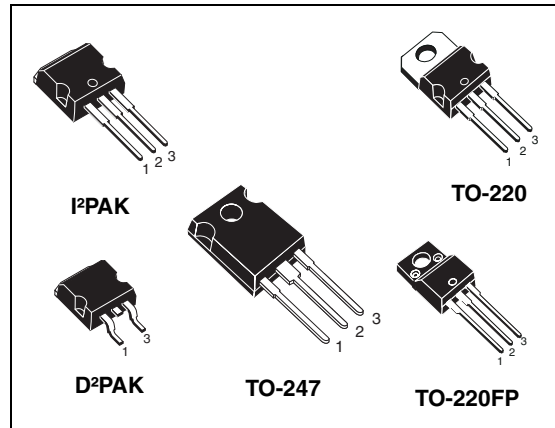
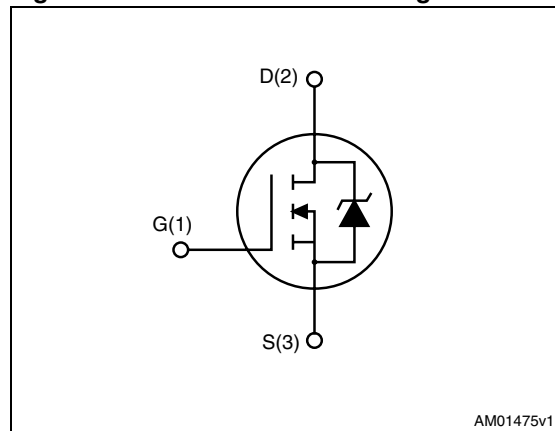


Figure 1. Internal schematic diagram



AM01475v1

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	9
4	Package mechanical data	10
5	Packaging mechanical data	16
6	Revision history	17

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, I ² PAK, D ² PAK, TO-247	TO-220FP	
V _{GS}	Gate-source voltage	25		V
I _D	Drain current (continuous) at T _C = 25 °C	17	17 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	10.7	10.7 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	68	68 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	125	30	W
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	5		A
E _{AS}	Single pulse avalanche energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	400		mJ
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)		2500	V
T _{stg}	Storage temperature	- 55 to 150		°C
T _j	Max. operating junction temperature	150		°C

1. Limited only by maximum temperature allowed

2. Pulse width limited by safe operating area

3. I_{SD} ≤ 17 A, di/dt ≤ 400 A/μs; V_{Peak} < V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	Value					Unit
		D ² PAK	I ² PAK	TO-220	TO-247	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	1			4.17	°C/W	
R _{thj-amb}	Thermal resistance junction-ambient max		62.5	50	62.5	°C/W	
R _{thj-pcb}	Thermal resistance junction-pcb max	30				°C/W	
T _l	Maximum lead temperature for soldering purpose	300					°C

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 8.5\text{ A}$		0.175	0.190	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1950	-	pF
C_{oss}	Output capacitance			46		pF
C_{rss}	Reverse transfer capacitance			3		pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0$	-	133	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related			44		pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	2.5	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 8.5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 20)	-	50	-	nC
Q_{gs}	Gate-source charge			23		nC
Q_{gd}	Gate-drain charge			13		nC

1. $C_{oss\text{ eq}}$ time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. $C_{oss\text{ eq}}$ energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_d (v)	Voltage delay time	$V_{DD} = 400$ V, $I_D = 11$ A,		37		ns
t_r (v)	Voltage rise time	$R_G = 4.7$ Ω , $V_{GS} = 10$ V	-	10	-	ns
t_f (i)	Current fall time	(see Figure 21)		12		ns
t_c (off)	Crossing time	(see Figure 24)		24		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		17	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		68	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 17$ A, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 17$ A, $di/dt = 100$ A/ μ s	-	264		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100$ V (see Figure 21)	-	4		nC
I_{RRM}	Reverse recovery current			28		A
t_{rr}	Reverse recovery time	$I_{SD} = 17$ A, $di/dt = 100$ A/ μ s	-	340		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100$ V, $T_j = 150$ °C	-	5		nC
I_{RRM}	Reverse recovery current	(see Figure 21)		29		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μ s, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK, I²PAK

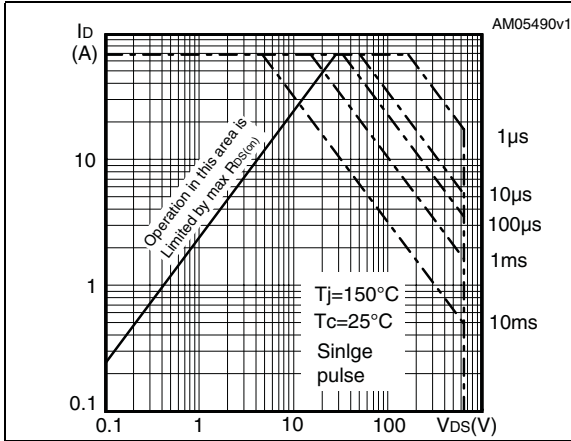


Figure 3. Thermal impedance for TO-220, D²PAK, I²PAK

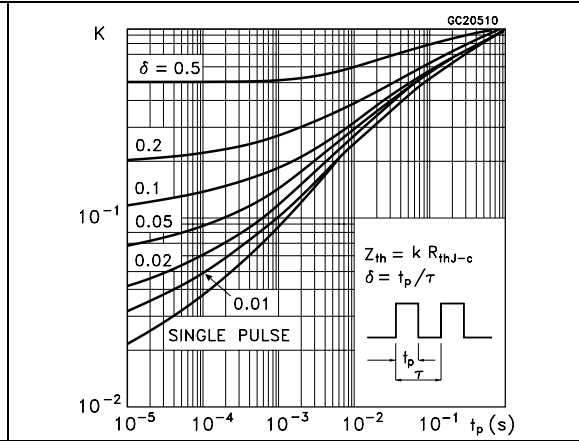


Figure 4. Safe operating area for TO-220FP

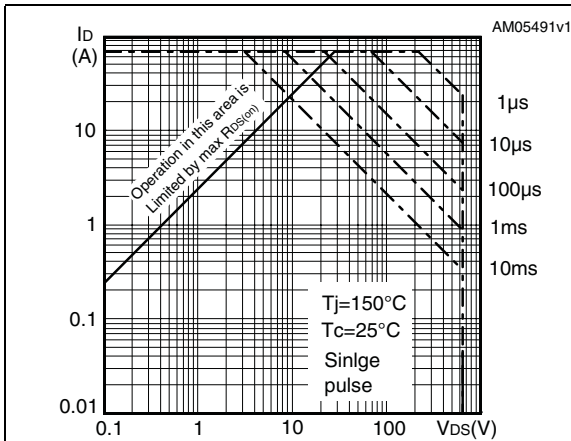


Figure 5. Thermal impedance for TO-220FP

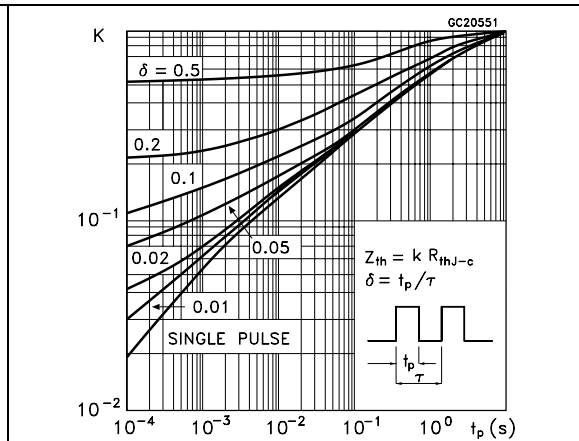


Figure 6. Safe operating area for TO-247

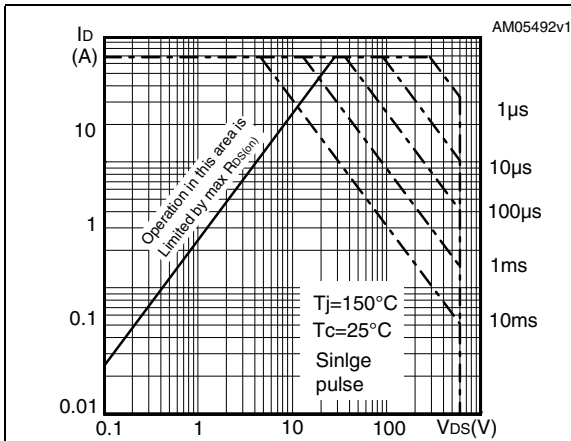


Figure 7. Thermal impedance for TO-247

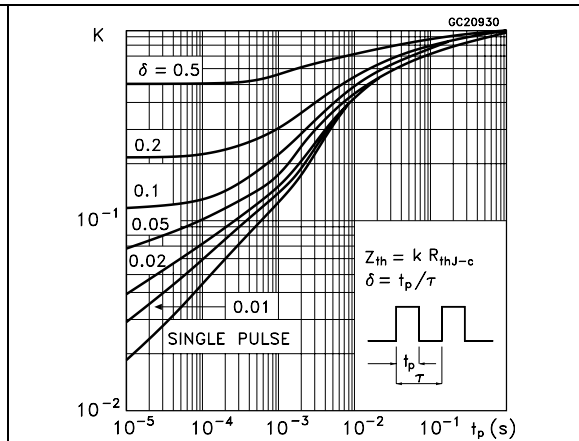


Figure 8. Output characteristics

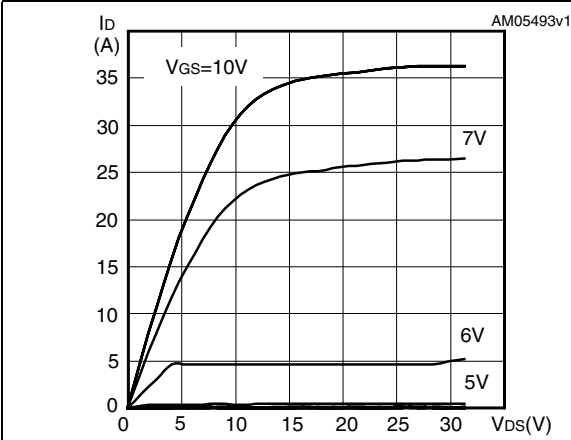


Figure 9. Transfer characteristics

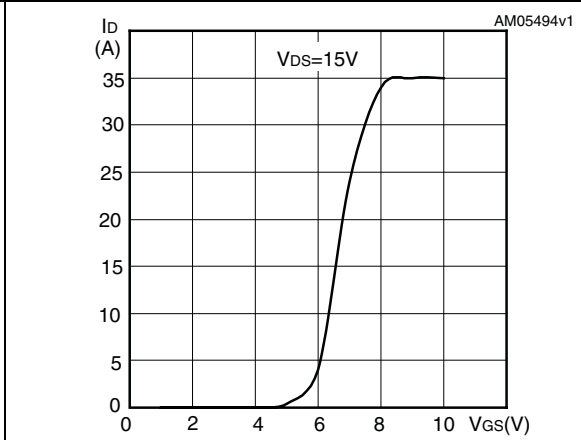


Figure 10. Gate charge vs gate-source voltage

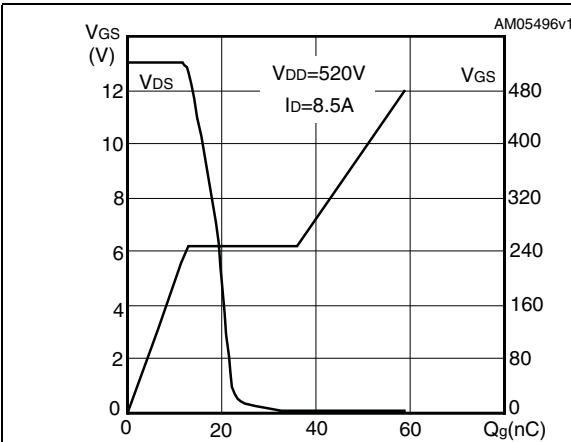


Figure 11. Static drain-source on resistance

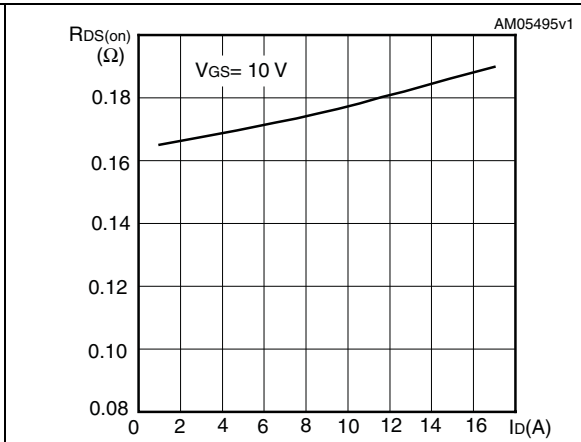


Figure 12. Capacitance variations

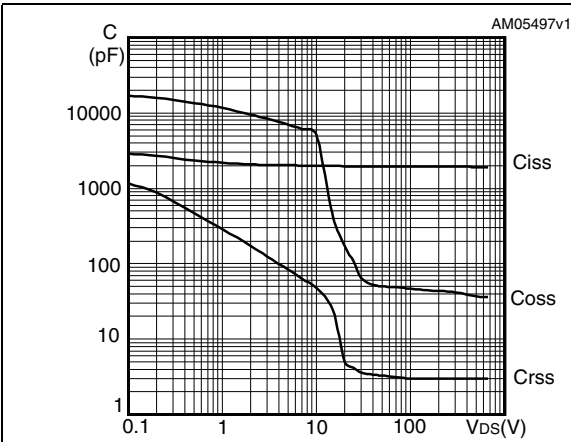


Figure 13. Output capacitance stored energy

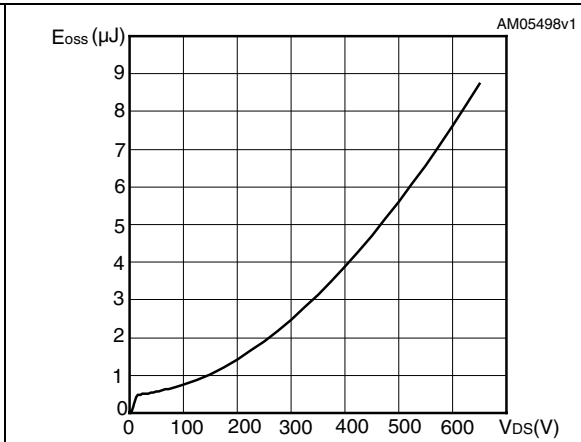


Figure 14. Normalized gate threshold voltage vs temperature

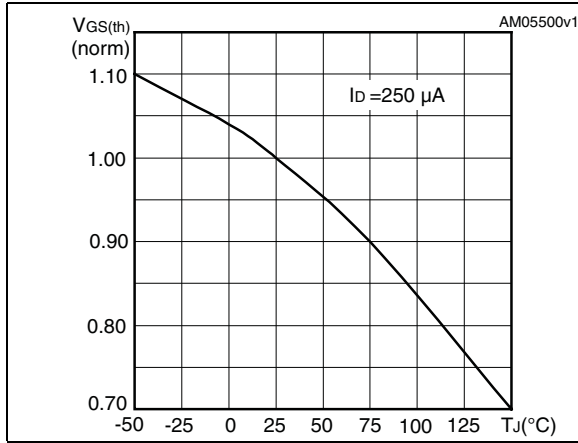


Figure 15. Normalized on resistance vs temperature

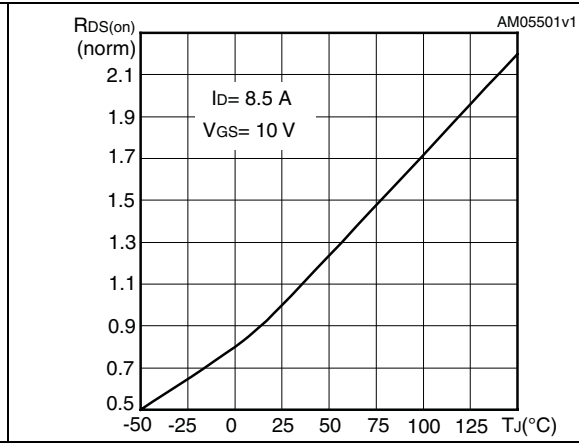


Figure 16. Source-drain diode forward characteristics

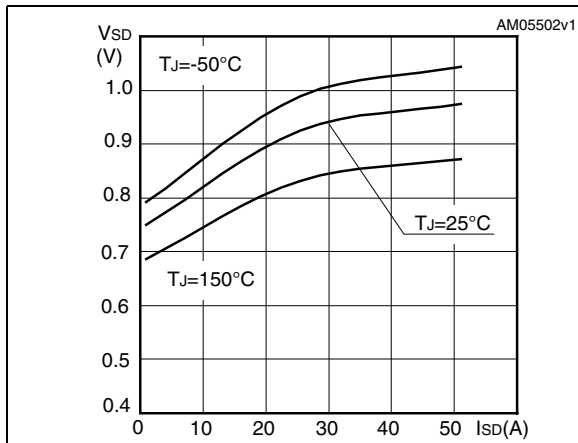


Figure 17. Normalized BV_{DSS} vs temperature

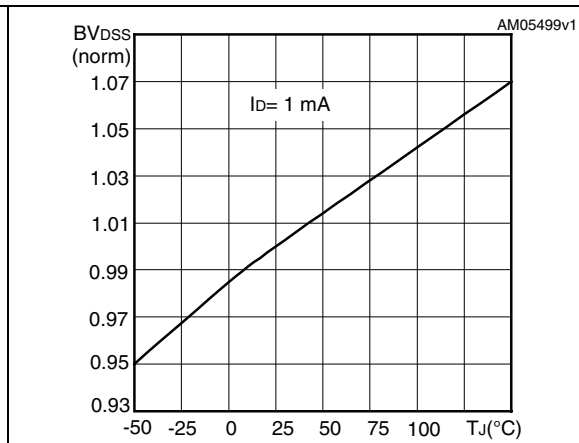
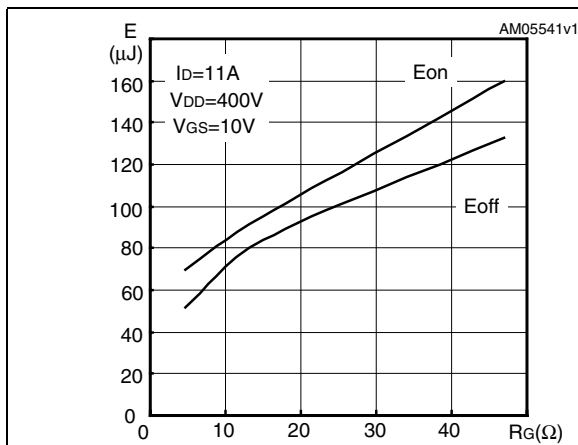


Figure 18. Switching losses vs gate resistance (1)



1. Eon including reverse recovery of a SiC diode

3 Test circuits

Figure 19. Switching times test circuit for resistive load

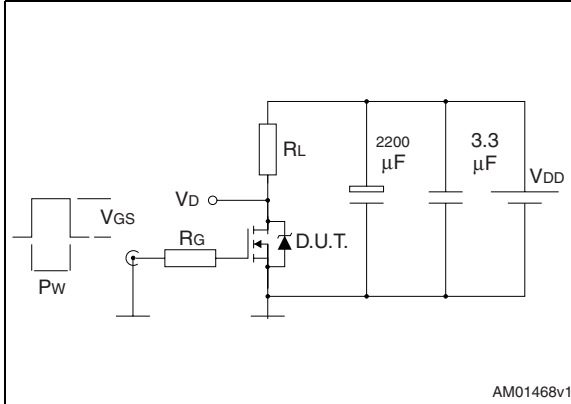


Figure 20. Gate charge test circuit

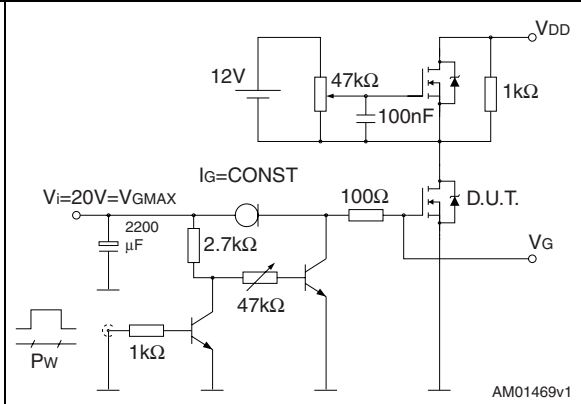


Figure 21. Test circuit for inductive load switching and diode recovery times

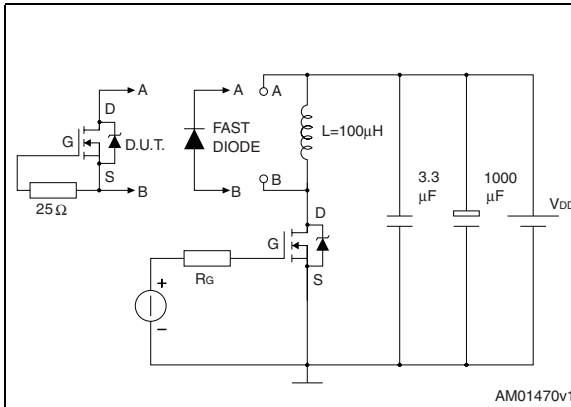


Figure 22. Unclamped inductive load test circuit

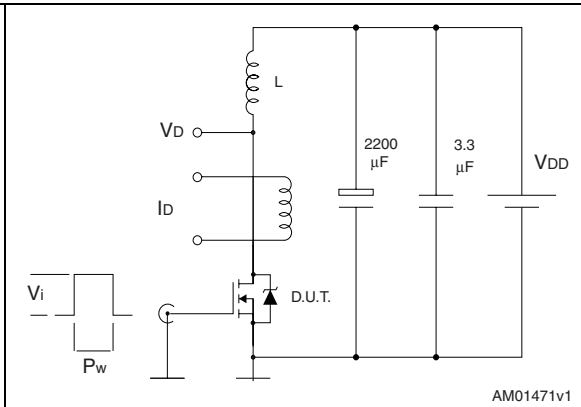


Figure 23. Unclamped inductive waveform

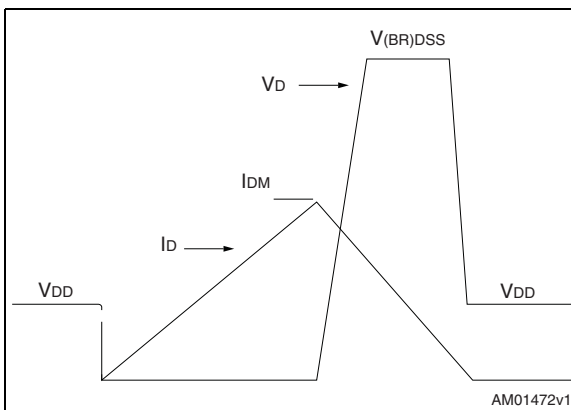
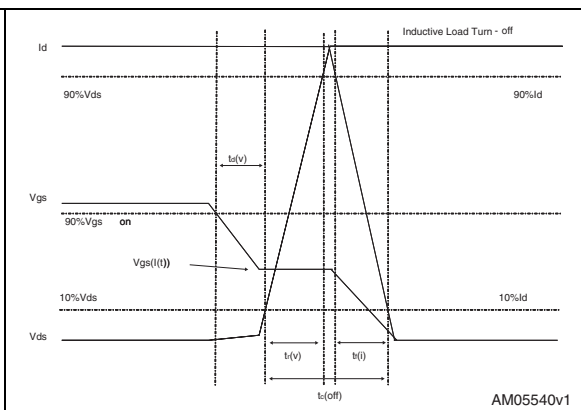


Figure 24. Switching time waveform



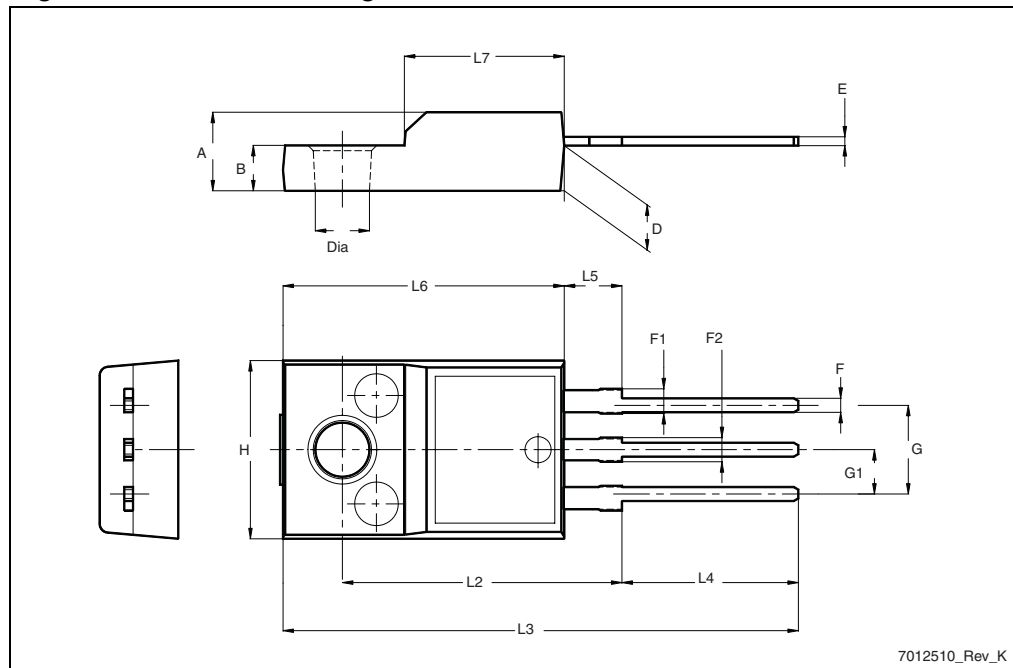
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. TO-220FP mechanical data

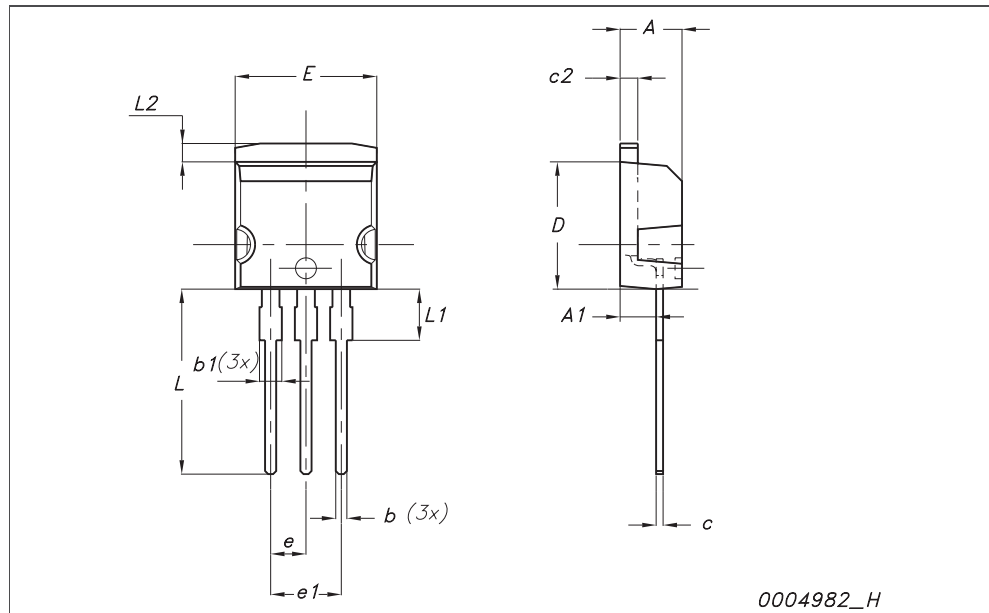
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 25. TO-220FP drawing mechanical data



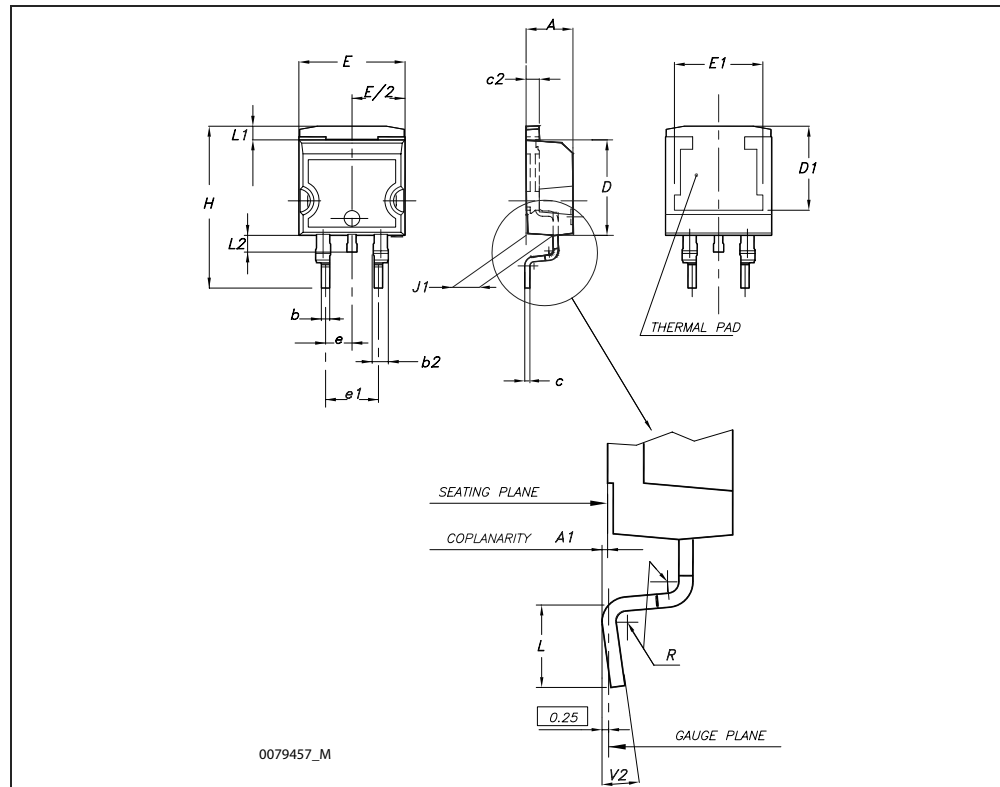
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



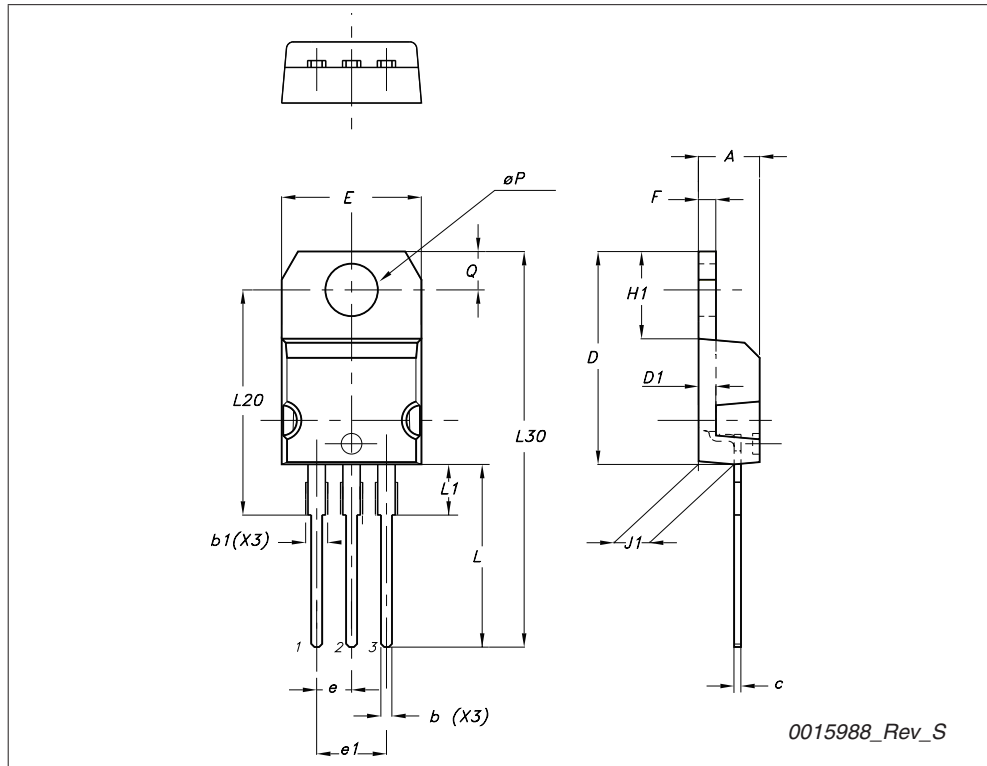
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



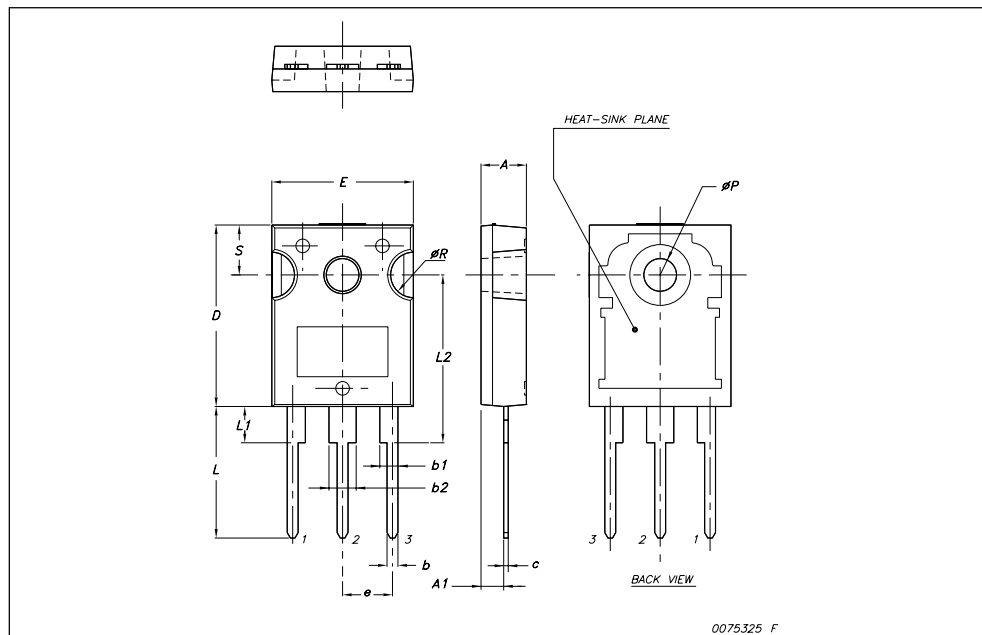
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



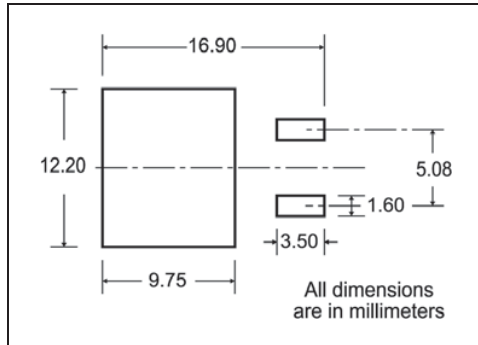
TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
$\varnothing P$	3.55		3.65
$\varnothing R$	4.50		5.50
S		5.50	



5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
24-Feb-2009	1	First release
27-Feb-2009	2	Corrected package information on first page.
11-Nov-2009	3	Document status promoted from preliminary data to datasheet.

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